

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 1, line 8 with:

The present invention relates to a semiconductor device using a metal silicate film as a gate insulating film, to a method for manufacturing such a semiconductor device, to an apparatus ~~being available~~ for forming such a film in ~~such a~~ semiconductor device, and to a method ~~being available~~ for forming such a high-dielectric-constant film in ~~such a~~ semiconductor device.